IN THE SPECIFICATION:

Paragraph beginning at lin 18 of page 4 has been am nded as follows:

According to the above optical waveguide probe, since the propagated light can be efficiently deflected at the bent portion, the efficiency of outgoing ~~of~~ light from the minute aperture, or the efficiency of the detection of light at the minute aperture can be improved. Further, since the propagated light having been propagated through the optical waveguide can be condensed to the minute aperture, or to the contrary, since the light from the minute aperture can be collimated, the efficiency can be improved.

Paragraph beginning at line 10 of page 14 has been amended as follows:

FIGS. 6A to 6J are views for explaining a manufacturing method of the optical waveguide probe 51. In the following, the upper side of the drawing is made as a front surface, and the lower side is made as a back surface. As shown in FIG. 6A, a start substrate (silicon on insulator substrate, hereinafter referred to as an SOI substrate) is used which includes a substrate 61 made of silicon, an oxide film 62 on the substrate 61, and an active layer 63 made of silicon formed on the oxide film. The active layer 63 and the substrate 61 are made of silicon single crystal of a (100)

plane. Although a direction of an orienting ~~oriental~~ flat of a (100) wafer is a <110> direction, in the start substrate of the present invention, the ~~oriental~~ orienting flat direction of the active layer 63 is made to deviate from that of the substrate 61 by 45 degrees. That is, in FIG. 6a, in FIG. 6a, the crystal orientation of the substrate 61 indicated by arrow A is the <110> direction, the crystal orientation of the active layer indicated by arrow B in the drawing is a <100> direction, and the directions are respectively coincident with optical axis directions of the optical fiber and the optical waveguide 2 fixed in the V groove. A mask 64 for step portion formation is formed on the active layer 63. Besides, a mask 65 for release is formed at the back surface side of the substrate 61. As materials of the mask for step portion formation and the mask 65 for release, a material having resistance to anisotropic etching using KOH, TMAH or the like, for example, silicon dioxide or silicon nitride is used.